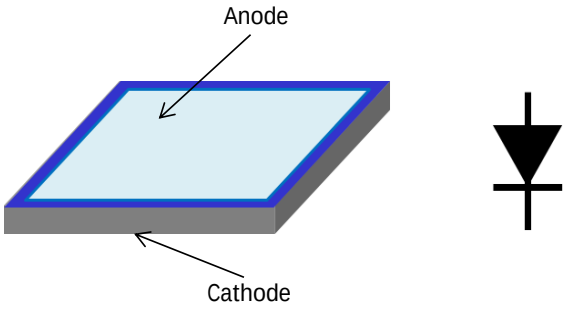
YJ Planar Schottky Barrier Diode Die Specification

30V 0.1A,13mil, Schottky barrier diode die based on silicon planar process
Part No.: PSB013L030AS-155A



Main Products Characterstics

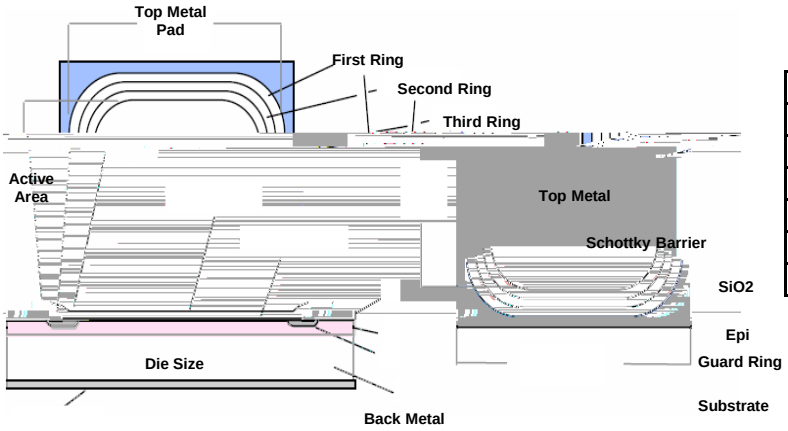
Maximum Ratings

Parameter	Symbol	Rating
Repetitive peak reverse voltage	V_{RRM}	30 V
Average forward current	$I_{F(AV)}$	0.1 A
(tp = 8.3 ms, halfwave, 1 cycle)	I_{FSM}	1 A
Storage temperature range	T_{stg}	-50 to +125 °C
Maximum operating junction temperature	T_j	125 °C

Static Electrical Characteristics (Ta = 25°C)

Parameter	Symbol	Value	
		Spec	Typical
Reverse breakdown voltage I_R = 1mA	V_{BR}	30 V	50V
Maximum forward voltage drop I_F = 0.1A 2%	V_F	0.6V	0.5V
Maximum reverse current V_R = 35V 2%	I_R	5uA	0.4uA

Device Schematics and Outline Drawing



Die Thickness *	155um
Die Size **	13 Mils
Top Metal Pad	11Mils
Active Area	6.4Mils
Top Metal	Al/3.5um
Back Metal	AG/1.5um
Steet width	50um

Note: 1 * : Also can offer device with 8 mils thickness
2 **: Cutting street width is around 1.5 mils

Important Notice

Specification apply to die only. Actual performance may degrade when assembled.

Yangjie Electronics does not guarantee device performance after assembly.
All operating parameters must be validated for each customer application by customer's technical experts.

Data sheet information is subjected to change without notice.

Recommended Storage Environment:

Store in original container, in dessicated nitrogen, with no contamination.

Shelf life for parts stored in above condition is 2 years.

If the storage is done in normal atmosphere shelf life is reduced to 6 months.